Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	30	("first power rail") and ("second power rail")	US-PGPUB	OR	OFF	2005/09/14 13:47
L2	3	("first power rail") and ("second power rail") and latch and "clock signal"	US-PGPUB	OR	OFF	2005/09/14 13:44
L3	4	("first power rail") and ("second power rail") and ("third power rail")	US-PGPUB	OR	OFF	2005/09/14 13:46

DB = East examiner initial: 2A

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10432	((stress adj2 test\$3) or (burn-in adj2 test\$3))	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 13:52
L7	76	((stress adj2 test\$3) or (burn-in adj2 test\$3) or (stress\$3 adj3 (device or IC or circuit))) and (power adj3 rail\$1)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 13:56
L8	7	((stress adj2 test\$3) or (burn-in adj2 test\$3) or (stress\$3 adj3 (device or IC or circuit))) and (power adj3 rail\$1) and latch\$3 and (clock adj2 signal\$1)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:04
L9	76	((stress adj2 test\$3) or (burn-in adj2 test\$3) or (stress\$3 adj3 (device or IC or circuit))) and (power adj3 rail\$1)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:05
L10	0	((stress adj2 test\$3) or (burn-in adj2 test\$3) or (stress\$3 adj3 (device or IC or circuit))) and (power adj3 rail\$1) and 714/726. ccls.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:05
L11	1	((stress adj2 test\$3) or (burn-in adj2 test\$3) or (stress\$3 adj3 (device or IC or circuit))) and (power adj3 rail\$1) and 326/16. ccls.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:06
L12	10	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and latch\$3 and (clock adj2 signal\$1)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:08
L13	5	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and latch\$3 and (clock adj2 signal\$1) and test\$4	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:13
L14	5	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and (latch\$3 or flip-flop\$) and (clock adj2 signal\$1) and test\$4	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:09
L15	3	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and (latch\$3 or flip-flop\$) and (clock adj2 signal\$1) and test\$4 and overlap\$6	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:10
L16	4	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff))	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:14

L17	1	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (clock adj2 signal)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:15
L18	1	(first adj2 power adj2 rail\$1) and (second adj2 power adj2 rail) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (test\$3 or stress\$4 or burn-in)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:16
L19	111	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (test\$3 or stress\$4 or burn-in)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:16
L20	46	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (first adj2 clock adj2 signal) and (second adj2 clock adj2 signal)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:17
L21	17	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (first adj2 clock adj2 signal) and (second adj2 clock adj2 signal) and (test\$4 or stress\$4 or burn-in)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:24
L22	1	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (first adj2 clock adj2 signal) and (second adj2 clock adj2 signal) and (test\$4 or stress\$4 or burn-in) and 714/726.ccls.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:18
L23	0	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (first adj2 clock adj2 signal) and (second adj2 clock adj2 signal) and (test\$4 or stress\$4 or burn-in) and 326/16.ccls.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:19
L24	0	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (first adj2 clock adj2 signal) and (second adj2 clock adj2 signal) and (test\$4 or stress\$4 or burn-in) and de-power\$3	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:20

Search History 9/14/05 2:46:35 PM Page 2
C:\Documents and Settings\EAbraham\My Documents\EAST\Workspaces\newformat.wsp

L25	2	(first adj2 power) and (second adj2 power) and (first adj2 (latch or flip-flop or ff)) and (second adj2 (latch or flip-flop or ff)) and (first adj2 clock adj2 signal) and (second adj2 clock adj2 signal) and (test\$4 or stress\$4 or burn-in) and overlap\$6	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:21
L26	4	(stress\$3 near3 (IC or (integrated circuit))) and 714/726.ccls.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:26
L27	13	((stress\$3 near3 (IC or (integrated circuit))) or (stress adj2 test\$3)) and 714/726.ccls.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:27
L28	0	((stress\$3 near3 (IC or (integrated circuit))) or (stress adj2 test\$3)) and 714/726.ccls. and (power adj3 rail\$1)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:39
L29	35	bernstein-kerry.in.	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:44
L33	2	bernstein-kerry.in. and (stress near2 test\$3)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:44
L34	5	bernstein-kerry.in. and (test\$3)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:46
L35	0	bernstein-kerry.in. and "power rail"	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/14 14:46



Home | Login | Logout | Access Information | Alerts |

Welcome United States Patent and Trademark Office

Search Results	BROWSE	31	
D 11 5 11/1/4			

Search Res	ults	882		BROWSE	SEARCH	IEEE XPLORE GUIDE	
Your search	"(((stress <near 3="">test)<o h matched 1145 of 1235060 h of 100 results are displaye</o </near>	6 documen	ts.			∭e-n der.	wii
» Search O	ptions						
<u>View Sessi</u>	on History			Search			
New Searc	<u>h</u>	(((stre	ss<	near/3>test) <or>(strssing<ne< td=""><td>ar/3>ic)<and>(pov</and></td><td>ver<near 3="">rail)<and>latche</and></near></td><td></td></ne<></or>	ar/3>ic) <and>(pov</and>	ver <near 3="">rail)<and>latche</and></near>	
			he	ck to search only within this	results set		
» Other Res (Available F	ources for Purchase)	Displ	ay	Format: © Citation (Citation & Ab	estract	
Top Book	Results	Select	A	rticle Information		View: 1-25 <u>2</u> 6	<u>3-5</u>
<u>Handbook</u> by Chan, H Hardcover, <u>System The</u>	Edition: 1 eory and Practical s of Biomedical Signals G. D.; Edition: 1		1.	Encapsulants Islam, M.S.; Suhling, J.C.; Components and Packagi	t. 2005 Page(s): .1109/TCAPT.20	005.854301	Cc
» Key		П	2	Optical stability of silico	n nitride MIS in	version laver solar cells	
IEEE JNL	IEEE Journal or Magazine			Jager, K.; Hezel, R.; Electron Devices, IEEE To		version layer solar dells	
IEE JNL	IEE Journal or Magazine			Volume 32, Issue 9, Sep	•		
IEEE CNF	IEEE Conference Proceeding			AbstractPlus Full Text: P	<u>'DF(</u> 688 KB) IE	EE JNL	
IEE CNF	IEE Conference Proceeding		3.	The current pulse rating lkeda, S.; Tsuda, S.; Wak	i, Y.;		
IEEE STD	IEEE Standard			Electron Devices, IEEE To Volume 17, Issue 9, Sep		90 - 693	
				AbstractPlus Full Text: P			
			4.	Low-high-low profile gal Heaton, J.L.; Walline, R.E Electron Devices, IEEE To Volume 26, Issue 1, Jan	.; Carroll, J.F.; ransactions on		
				AbstractPlus Full Text: P	<u>DF(</u> 888 KB) IE	EE JNL	
			5.	New concerns about into Peck, D.S.; Electron Devices, IEEE To Volume 26, Issue 1, Jan AbstractPlus Full Text: P	ransactions on 1979 Page(s):38	3 - 43	
				<u>rustractifus</u> Full Text. F	<u>ui (</u> ui 2 ND) IE	EE JIVE	
			6.	Thermal analysis of elec	tromigration te	st structures	

Electron Devices, IEEE Transactions on

Schafft, H.A.;

Volume 34, Issue 3, Mar 1987 Page(s):664 - 672 AbstractPlus | Full Text: PDF(944 KB) IEEE JNL 7. On the Relationship of Semiconductor Yield and Reliability П Kim, K.O.; Zuo, M.J.; Kuo, W.; Semiconductor Manufacturing, IEEE Transactions on Volume 18, Issue 3, Aug. 2005 Page(s):422 - 429 Digital Object Identifier 10.1109/TSM.2005.852110 AbstractPlus | Full Text: PDF(416 KB) IEEE JNL 8. MOS RF reliability subject to dynamic voltage stress-modeling and analy: Chuanzhao Yu; Yuan, J.S.; Electron Devices, IEEE Transactions on Volume 52, Issue 8, Aug. 2005 Page(s):1751 - 1758 Digital Object Identifier 10.1109/TED.2005.852546 AbstractPlus | Full Text: PDF(792 KB) IEEE JNL 9. Mechanical properties of YBaCuO formed on Ni-based alloy substrates w Shikimachi, K.; Kashima, N.; Nagaya, S.; Muroga, T.; Miyata, S.; Watanabe, T. Izumi, T.; Shiohara, Y.; Applied Superconductivity, IEEE Transactions on Volume 15, Issue 2, Part 3, June 2005 Page(s):3548 - 3551 Digital Object Identifier 10.1109/TASC.2005.849356 AbstractPlus | Full Text: PDF(1696 KB) IEEE JNL 10. Design of a 800 kJ HTS SMES Tixador, P.; Bellin, B.; Deleglise, M.; Vallier, J.C.; Bruzek, C.E.; Pavard, S.; Sa Applied Superconductivity, IEEE Transactions on Volume 15, Issue 2, Part 2, June 2005 Page(s):1907 - 1910 Digital Object Identifier 10.1109/TASC.2005.849331 AbstractPlus | Full Text: PDF(424 KB) IEEE JNL 11. The reliability of semiconductor devices in the bell system Peck, D.S.; Zierdt, C.H., Jr.; Proceedings of the IEEE Volume 62, Issue 2, Feb. 1974 Page(s):185 - 211 AbstractPlus | Full Text: PDF(3134 KB) IEEE JNL 12. Semiconductor network reliability assessment П Adams, J.; Workman, W.; Proceedings of the IEEE Volume 52, Issue 12, Dec. 1964 Page(s):1624 - 1635 AbstractPlus | Full Text: PDF(4191 KB) IEEE JNL 13. The Electrical Degradation of a Low-Loss Capacitor Prepared by Sinterin Mikoda, M.; Hikino, T.; Hayakawa, S.; Parts, Materials and Packaging, IEEE Transactions on Volume 3, Issue 1, Mar 1967 Page(s):8 - 13 AbstractPlus | Full Text: PDF(904 KB) IEEE JNL 14. Thin-Film Al-Al2O3-Al Capacitors Martin, J.; Parts, Materials and Packaging, IEEE Transactions on Volume 1, Issue 1, Jun 1965 Page(s):267 - 276 AbstractPlus | Full Text: PDF(1088 KB) IEEE JNL

15. Design of a Single Stress-Relaxation Test for Pressure Connections Goel, R.; Parts, Hybrids, and Packaging, IEEE Transactions on Volume 13, Issue 3, Sep 1977 Page(s):198 - 202 AbstractPlus Full Text: PDF(824 KB) IEEE JNL
16. Application of the Eyring Model to Capacitor Aging Data Endicott, H.; Hatch, B.; Sohmer, R.; Component Parts, IEEE Transactions on Volume 12, Issue 1, Mar 1965 Page(s):34 - 41 AbstractPlus Full Text: PDF(1248 KB) IEEE JNL
17. Approach to Developing Electrical Connection Comparison Data Through Testing Geshner, R.; Taylor, B.; Component Parts, IEEE Transactions on Volume 11, Issue 2, Jun 1964 Page(s):385 - 393 AbstractPlus Full Text: PDF(1176 KB) IEEE JNL
18. A Photo-Patternable Stress Relief Material for Plastic Packaged Integrate Cagan, M.; Ridley, D.; Components, Hybrids, and Manufacturing Technology, IEEE Transactions on Trans. on Components, Packaging, and Manufacturing Technology, Part A, B, Volume 11, Issue 4, Dec 1988 Page(s):611 - 617 <u>AbstractPlus</u> Full Text: <u>PDF</u> (1576 KB) IEEE JNL
19. Reliability of Metallized Ceramic/Polyimide Substrates Homa, T.; Posocco, A.; Components, Hybrids, and Manufacturing Technology, IEEE Transactions on Trans. on Components, Packaging, and Manufacturing Technology, Part A, B, Volume 9, Issue 4, Dec 1986 Page(s):396 - 402 AbstractPlus Full Text: PDF(904 KB) IEEE JNL
20. Role of Reliability and Accelerated Testing in VHSIC Technology Malik, S.; Components, Hybrids, and Manufacturing Technology, IEEE Transactions on Trans. on Components, Packaging, and Manufacturing Technology, Part A, B, Volume 5, Issue 1, Mar 1982 Page(s):138 - 141 AbstractPlus Full Text: PDF(480 KB) IEEE JNL
21. Controlled Electromigration for Field Failure Acceleration Juskey, F.; Components, Hybrids, and Manufacturing Technology, IEEE Transactions on Trans. on Components, Packaging, and Manufacturing Technology, Part A, B, Volume 10, Issue 3, Sep 1987 Page(s):370 - 373 AbstractPlus Full Text: PDF(480 KB) IEEE JNL
22. Accelerated Reliability Evaluation of Trimetal Integrated Circuit Chips in I Gallace, L.; Jacobus, L.; Pfiffner, E.; West, C.; Components, Hybrids, and Manufacturing Technology, IEEE Transactions on I Trans. on Components, Packaging, and Manufacturing Technology, Part A, B, Volume 2, Issue 2, Jun 1979 Page(s):172 - 179 AbstractPlus Full Text: PDF(1128 KB) IEEE JNL
23. Reliability Evaluation of Aluminum-Metallized MOS Dynamic RAM's in Plain High Humidity and Temperature Environments Striny, K.; Schelling, A.;

Components, Hybrids, and Manufacturing Technology, IEEE Transactions on [Trans. on Components, Packaging, and Manufacturing Technology, Part A, B, Volume 4, Issue 4, Dec 1981 Page(s):476 - 481 AbstractPlus | Full Text: PDF(832 KB) IEEE JNL 24. Stress testing FET gates without the use of test patterns Puri, Y.; Solid-State Circuits, IEEE Journal of Volume 10, Issue 5, Oct 1975 Page(s):294 - 298 AbstractPlus | Full Text: PDF(448 KB) | IEEE JNL 25. Strength assurance for stress-induced polarization-holding fibers Abe, T.; Mitsunaga, Y.; Koga, H.; Lightwave Technology, Journal of Volume 5, Issue 8, Aug 1987 Page(s):1089 - 1094 AbstractPlus | Full Text: PDF(1784 KB) IEEE JNL View Selected Hems View: 1-25 | 26-5

Minspec

Help Contact Us Privacy &:

© Copyright 2005 IEEE -